

# LH52256C/CH

CMOS 256K (32K × 8) Static RAM

## FEATURES

- 32,768 × 8 bit organization
- Access time: 70 ns (MAX.)
- Supply current:
  - Operating: 45 mA (MAX.)
  - 10 mA (MAX.) ( $t_{RC}$ ,  $t_{WC} = 1 \mu s$ )
  - Standby: 40  $\mu A$  (MAX.)
- Data retention current: 1.0  $\mu A$  (MAX.)
  - ( $V_{CCDR} = 3 V$ ,  $T_A = 25^\circ C$ )
- Wide operating voltage range:
  - 4.5 V  $\pm$  5.5 V
- Operating temperature:
  - Commerical temperature 0°C to +70°C
  - Industrial temperature -40° to +85°C
- Fully-static operation
- Three-state outputs
- Not designed or rated as radiation hardened
- Package:
  - 28-pin, 600-mil DIP
  - 28-pin, 450-mil SOP
  - 28-pin, 300-mil SK-DIP
  - 28-pin, 8 × 3 mm<sup>2</sup> TSOP (Type I)
- N-type bulk silicon

## DESCRIPTION

The LH52256C is a Static RAM organized as 32,768 × 8 bits which provides low-power standby mode. It is fabricated using silicon-gate CMOS process technology.

## PIN CONNECTIONS

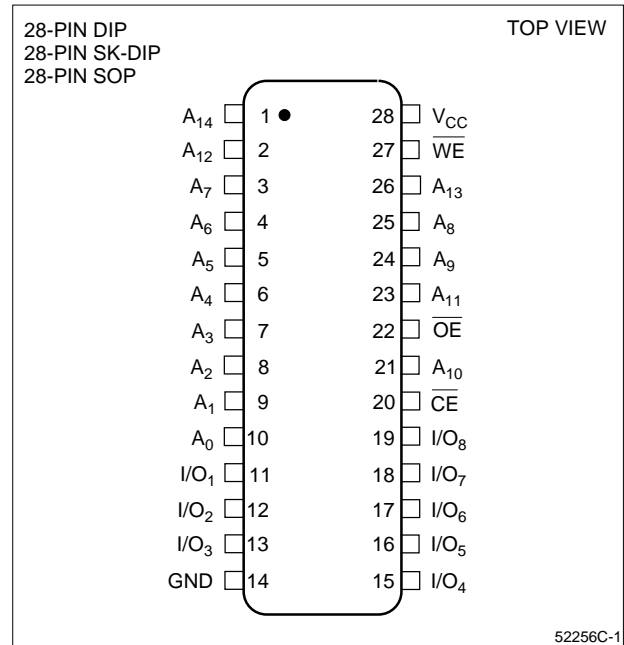


Figure 1. Pin Connections

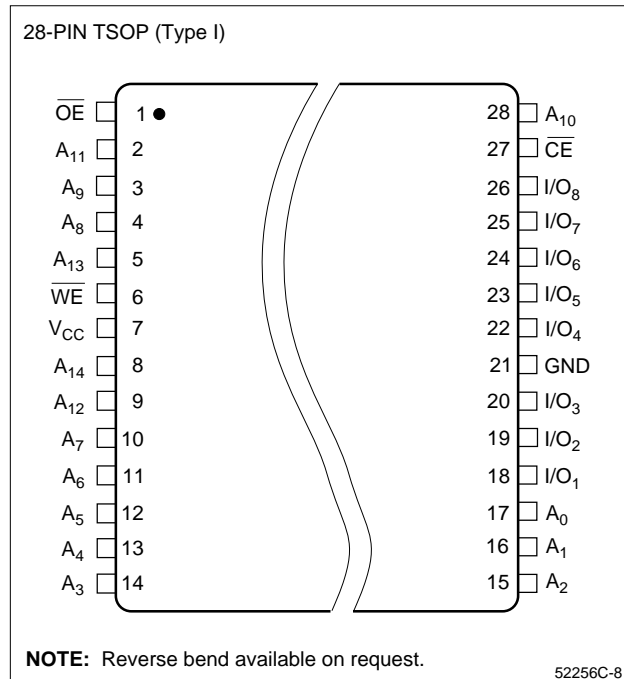


Figure 2. TSOP (Type I) Pin Connections

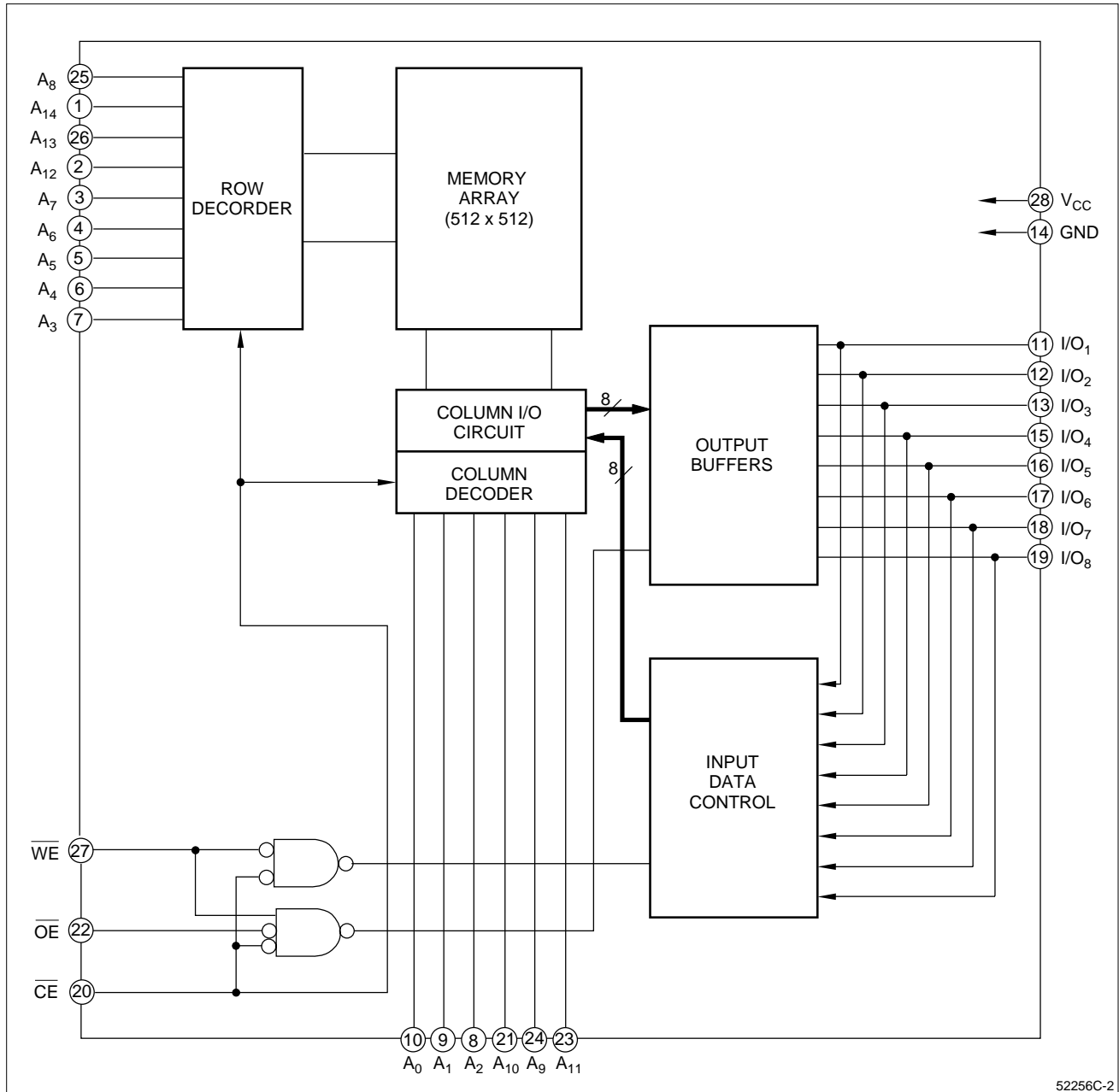


Figure 3. LH52256C Block Diagram

**PIN DESCRIPTION**

SIGNAL	PIN NAME
A <sub>0</sub> - A <sub>14</sub>	Address inputs
CE	Chip enable
WE	Write enable
OE	Output enable

SIGNAL	PIN NAME
I/O <sub>1</sub> - I/O <sub>8</sub>	Data inputs and outputs
V <sub>CC</sub>	Power supply
GND	Ground

**TRUTH TABLE**

$\overline{CE}$	$\overline{WE}$	$\overline{OE}$	MODE	I/O <sub>1</sub> - I/O <sub>8</sub>	SUPPLY CURRENT	NOTE
H	X	X	Standby	High impedance	Standby (I <sub>SB</sub> )	1
L	H	L	Read	Data output	Active (I <sub>CC</sub> )	1
L	H	H	Output disable	High impedance	Active (I <sub>CC</sub> )	1
L	L	X	Write	Data input	Active (I <sub>CC</sub> )	1

**NOTE:**

1. X = Don't care, L = Low, H = High

**ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	RATING	UNIT	NOTE
Supply voltage	V <sub>CC</sub>	-0.5 to +7.0	V	1
Input voltage	V <sub>IN</sub>	-0.5 to V <sub>CC</sub> + 0.5	V	1, 2
Operating temperature	T <sub>OPR</sub>	0 to +70	°C	—
Storage temperature	T <sub>STG</sub>	-65 to +150	°C	—

**NOTES:**

1. The maximum applicable voltage on any pin with respect to GND.
2. Undershoot of -3.0 V is allowed width of pulse below 50 ns.

**RECOMMENDED DC OPERATING CONDITIONS (T<sub>A</sub> = 0°C to +70°C)**

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	NOTE
Supply voltage	V <sub>CC</sub>	4.5	5.0	5.5	V	—
Input voltage	V <sub>IH</sub>	2.2	—	V <sub>CC</sub> + 0.5	V	—
	V <sub>IL</sub>	-0.5	—	0.8	V	1

**NOTE:**

1. Undershoot of -3.0 V is allowed width of pulse below 50 ns.

**DC ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 0°C to +70°C, V<sub>CC</sub> = 4.5 V to 5.5 V)**

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Input leakage current	I <sub>LI</sub>	V <sub>IN</sub> = 0 V to V <sub>CC</sub>	-1.0	—	1.0	μA
Output leakage current	I <sub>LO</sub>	CE = V <sub>IH</sub> or OE = V <sub>IH</sub> V <sub>IO</sub> = 0 V to V <sub>CC</sub>	-1.0	—	1.0	μA
Operating supply current	I <sub>CC</sub>	Minimum cycle, V <sub>IN</sub> = V <sub>IL</sub> or V <sub>IH</sub> I <sub>IO</sub> = 0 mA, CE = V <sub>IL</sub>	—	25	45.0	mA
	I <sub>CC1</sub>	t <sub>RC</sub> , t <sub>WC</sub> = 1 μs, V <sub>IN</sub> = V <sub>IL</sub> or V <sub>IH</sub> , I <sub>IO</sub> = 0 mA, CE = V <sub>IL</sub>	—	—	10.0	
Standby current	I <sub>SB</sub>	CE ≥ V <sub>CC</sub> - 0.2 V	—	0.6	40.0	μA
	I <sub>SB1</sub>	CE = V <sub>IH</sub>	—	—	3.0	mA
Output voltage	V <sub>OL</sub>	I <sub>OL</sub> = 2.1 mA	—	—	0.4	V
	V <sub>OH</sub>	I <sub>OH</sub> = -1.0 mA	2.4	—	—	

**NOTE:**

Typical values at V<sub>CC</sub> = 5.0 V, T<sub>A</sub> = 25°C

**AC ELECTRICAL CHARACTERISTICS  
AC Test Conditions**

PARAMETER	MODE	NOTE
Input pulse level	0.6 V to 2.4 V	—
Input rise and fall time	10 ns	—
Input and output timing Ref. level	1.5 V	—
Output load	1 TTL + C <sub>L</sub> (100 pF)	1

**NOTE:**

1. Including scope and jig capacitance.

**READ CYCLE (T<sub>A</sub> = 0°C to +70°C, V<sub>CC</sub> = 4.5 V to 5.5 V)**

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	NOTE
Read cycle time	t <sub>RC</sub>	70	—	ns	—
Address access time	t <sub>AA</sub>	—	70	ns	—
CE access time	t <sub>ACE</sub>	—	70	ns	—
Output enable to output valid	t <sub>OE</sub>	—	35	ns	—
Output hold from address change	t <sub>OH</sub>	10	—	ns	—
CE Low to output active	t <sub>LZ</sub>	10	—	ns	1
OE Low to output active	t <sub>OLZ</sub>	5	—	ns	1
CE High to output in High impedance	t <sub>HZ</sub>	0	30	ns	1
OE High to output in High impedance	t <sub>OHZ</sub>	0	30	ns	1

**NOTES:**

1. Active output to high-impedance and high-impedance to output active tests specified for a ±200 mV transition from steady state levels into the test load.

**WRITE CYCLE ( $T_A = 0^\circ\text{C}$  to  $+70^\circ\text{C}$ ,  $V_{CC} = 4.5\text{ V}$  to  $5.5\text{ V}$ )**

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	NOTE
Write cycle time	$t_{WC}$	70	—	ns	—
CE Low to end of write	$t_{CW}$	45	—	ns	—
Address valid to end of write	$t_{AW}$	45	—	ns	—
Address setup time	$t_{AS}$	0	—	ns	—
Write pulse width	$t_{WP}$	35	—	ns	—
Write recovery time	$t_{WR}$	0	—	ns	—
Input data setup time	$t_{DW}$	30	—	ns	—
Input data hold time	$t_{DH}$	0	—	ns	—
$\overline{WE}$ High to output active	$t_{OW}$	5	—	ns	1
$\overline{WE}$ Low to output in High impedance	$t_{WZ}$	0	30	ns	1
$\overline{OE}$ High to output in High impedance	$t_{OHZ}$	0	30	ns	1

**NOTE:**

- Active output to high-impedance and high-impedance to output active tests specified for a  $\pm 200\text{ mV}$  transition from steady state levels into the test load.

**CAPACITANCE ( $T_A = 25^\circ\text{C}$ ,  $f = 1\text{ MHz}$ )**

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNIT	NOTE
Input capacitance	$C_{IN}$	$V_{IN} = 0\text{ V}$	—	—	7	pF	1
I/O capacitance	$C_{I/O}$	$V_{I/O} = 0\text{ V}$	—	—	10	pF	1

**NOTE:**

- This parameter is sampled and not production tested.

**DATA RETENTION CHARACTERISTICS ( $T_A = 0^\circ\text{C}$  to  $+70^\circ\text{C}$ )**

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNIT	NOTE	
Data retention supply voltage	$V_{CCDR}$	$\overline{CE} \geq V_{CCDR} - 0.2\text{ V}$	2.0	—	5.5	V	—	
Data retention supply current	$I_{CCDR}$	$V_{CCDR} = 3.0\text{ V}$	$T_A = 25^\circ\text{C}$	—	0.3	1.0	$\mu\text{A}$	—
			$T_A = 40^\circ\text{C}$	—	—	3.0		—
		$\overline{CE} \geq V_{CCDR} - 0.2\text{ V}$					15	
Chip enable setup time	$t_{CDR}$	—	0	—	—	ns	—	
Chip enable hold time	$t_R$	—	$t_{RC}$	—	—	ns	1	

**NOTE:**

- $t_{RC}$  = Read cycle time.
- Typical values at  $T_A = 25^\circ\text{C}$

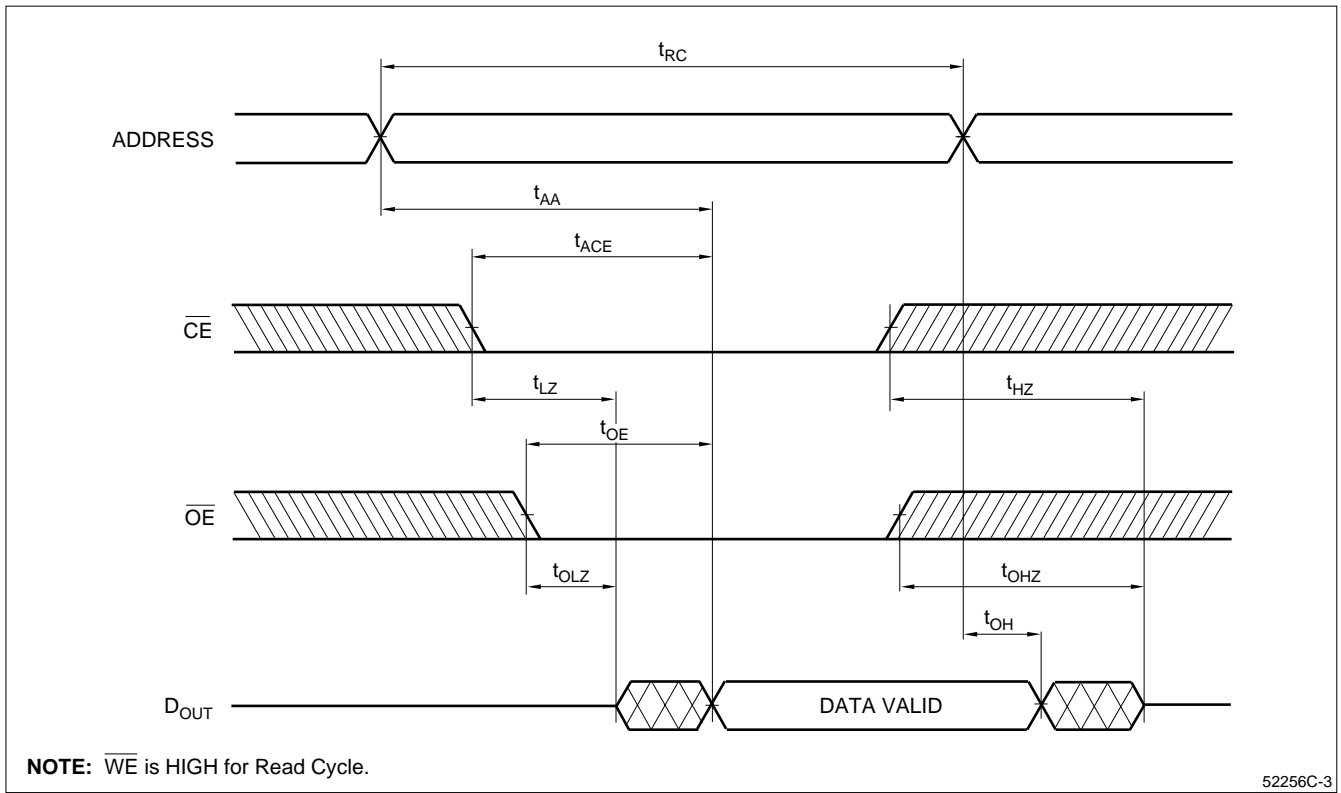
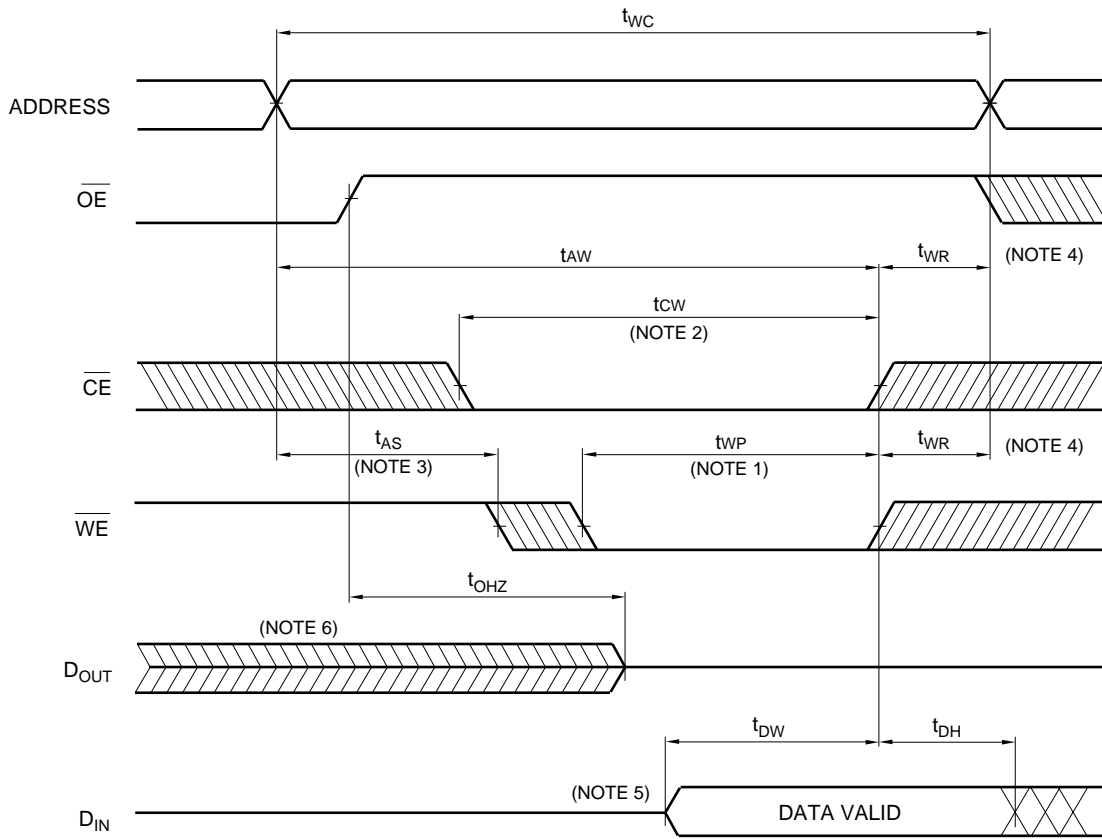


Figure 4. Read Cycle

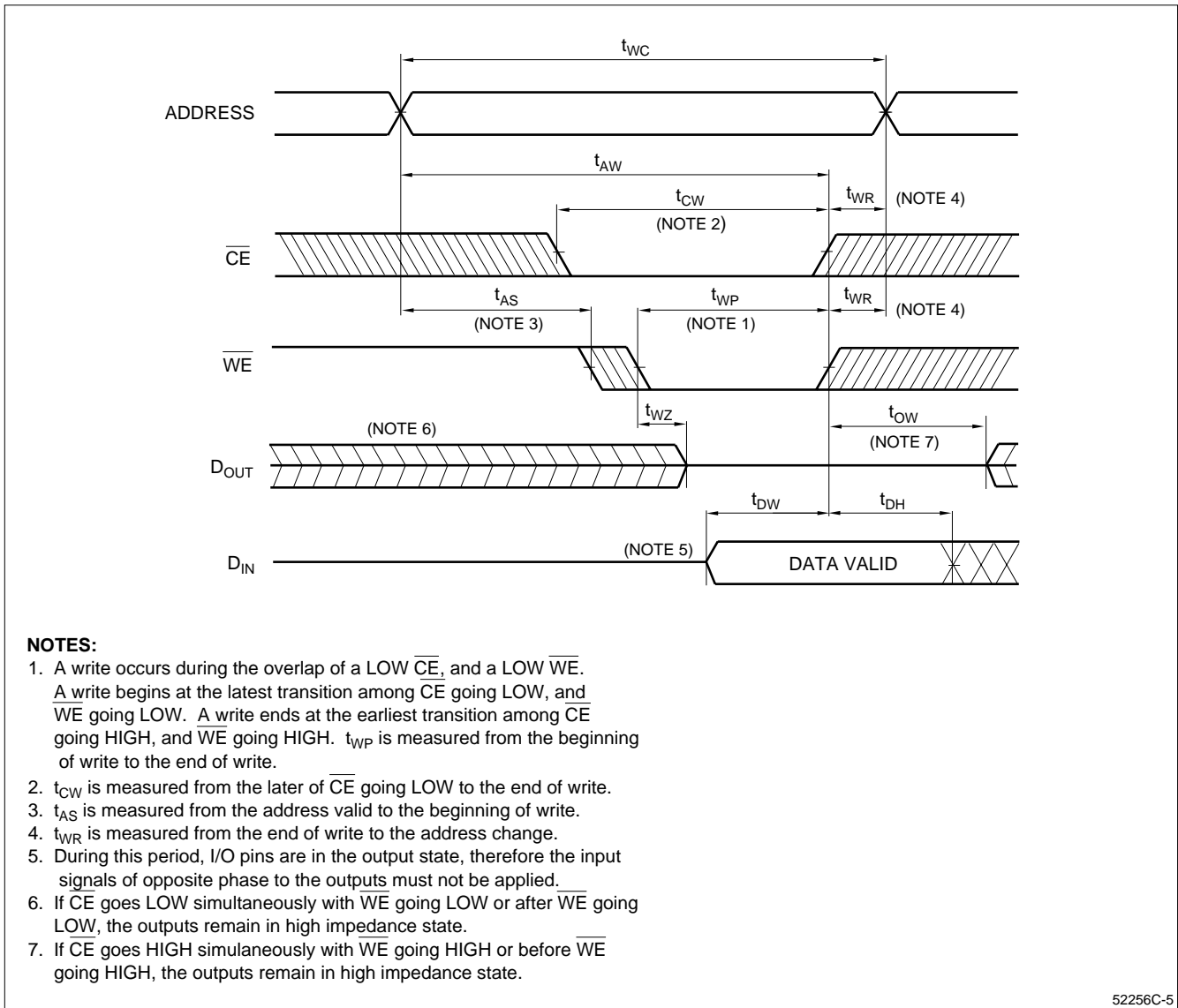


**NOTES:**

1. A write occurs during the overlap of a LOW  $\overline{CE}$ , and a LOW  $\overline{WE}$ . A write begins at the latest transition among  $\overline{CE}$  going LOW, and  $\overline{WE}$  going LOW. A write ends at the earliest transition among  $\overline{CE}$  going HIGH, and  $\overline{WE}$  going HIGH.  $t_{WP}$  is measured from the beginning of write to the end of write.
2.  $t_{CW}$  is measured from the later of  $\overline{CE}$  going LOW to the end of write.
3.  $t_{AS}$  is measured from the address valid to the beginning of write.
4.  $t_{WR}$  is measured from the end of write to the address change.
5. During this period, I/O pins are in the output state, therefore the input signals of opposite phase to the outputs must not be applied.
6. If  $\overline{CE}$  goes LOW simultaneously with  $\overline{WE}$  going LOW or after  $\overline{WE}$  going LOW, the outputs remain in high impedance state.
7. If  $\overline{CE}$  goes HIGH simultaneously with  $\overline{WE}$  going HIGH or before  $\overline{WE}$  going HIGH, the outputs remain in high impedance state.

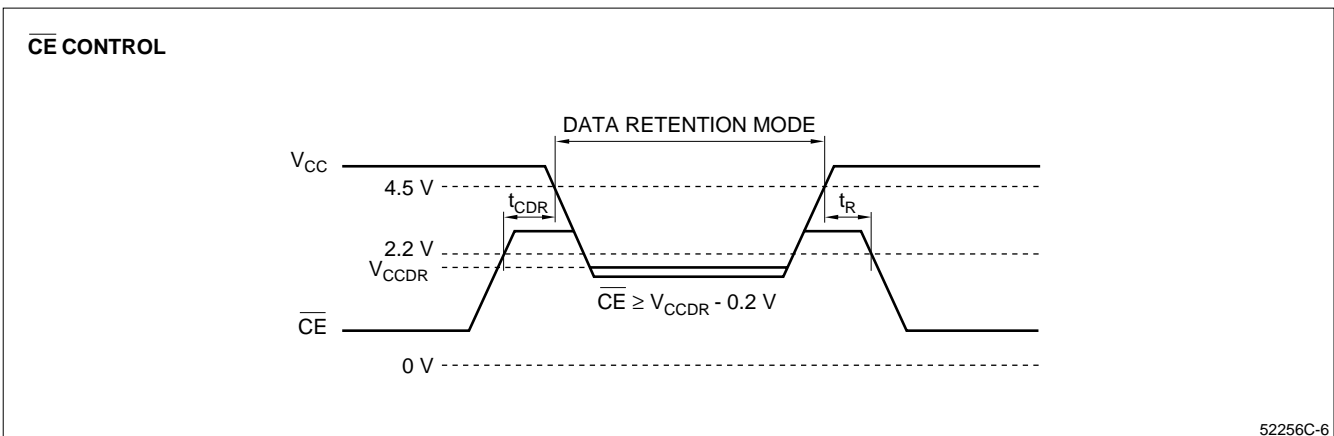
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**Figure 5. Write Cycle (OE Controlled)**



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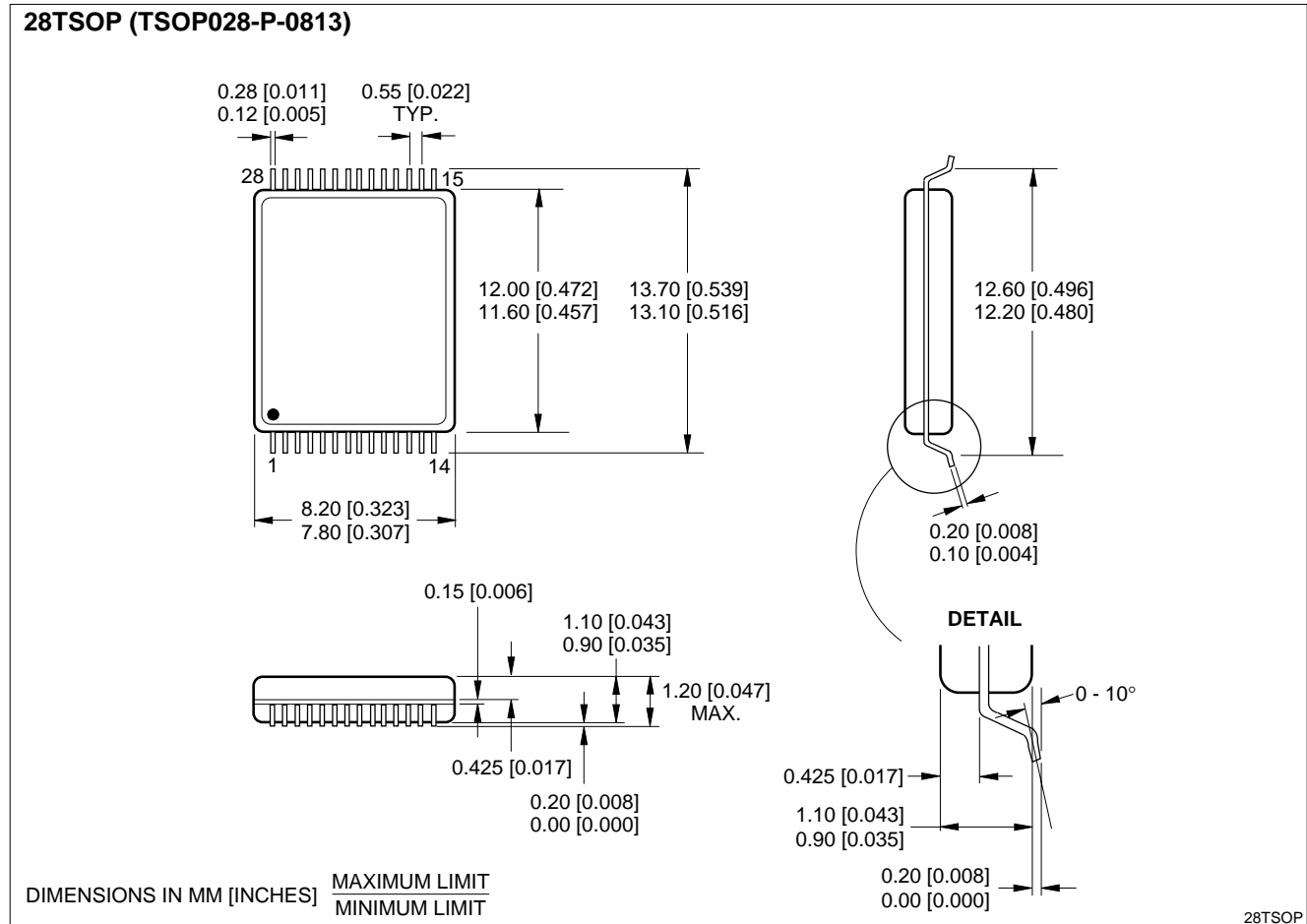
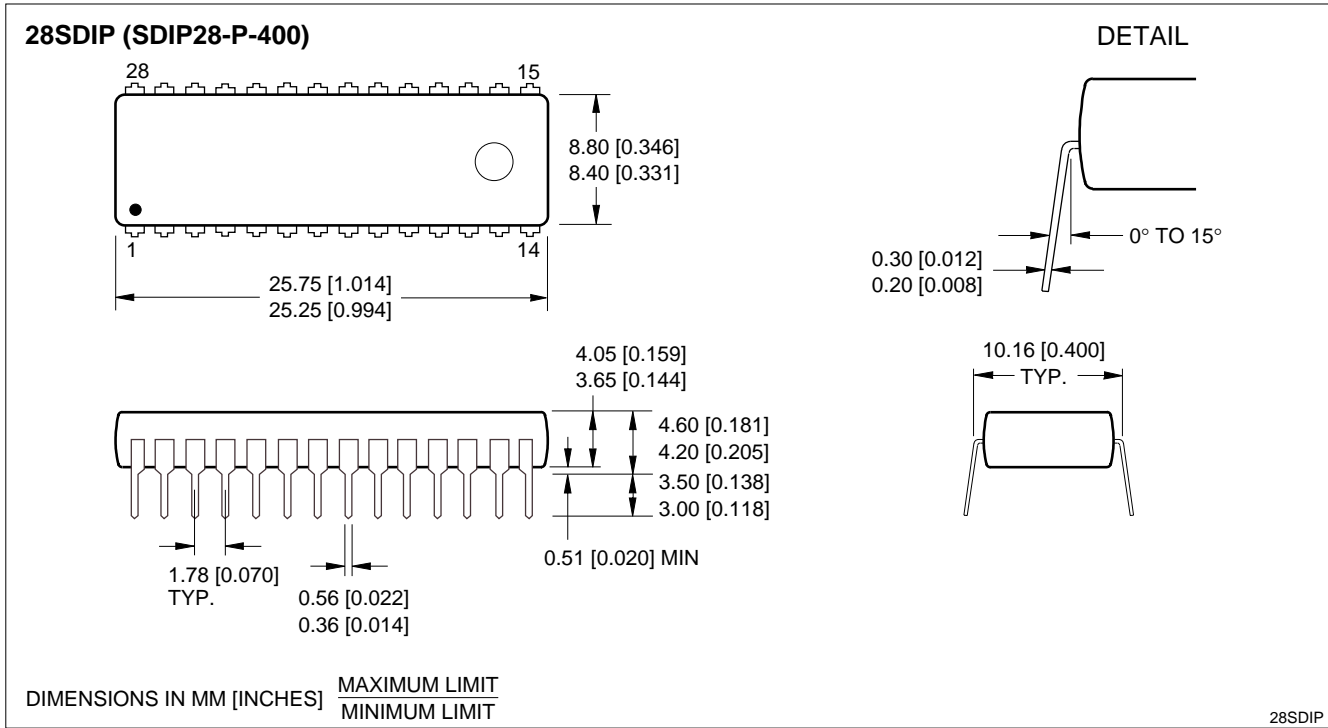
Figure 6. Write Cycle ( $\overline{OE}$  Low Fixed)



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**ORDERING INFORMATION**

